

# Post-CMP Defect



CMP (backend) . CMP (backend)

CMP backend . CMP .

CMP radial . 1 . 1 . CMP .

가 blanket (film) . film 1%

CMP (polish rate) . 가 . 가

, carrier , wafer carrier (platen) ,

chemicals ,

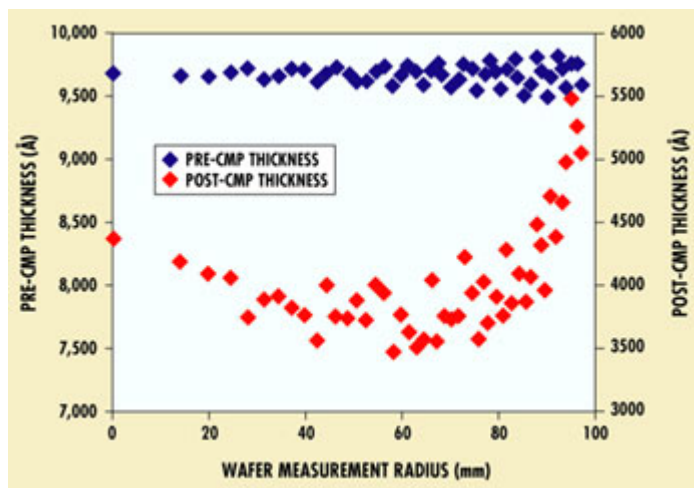
CMP / blanket film .

가 film layer . (standard area), (polar map), (standard setup)

line (diameter scan) .

order radial film monotonic radial . film higher-

CMP 가 .



## 1. CMP

2 (site selection)

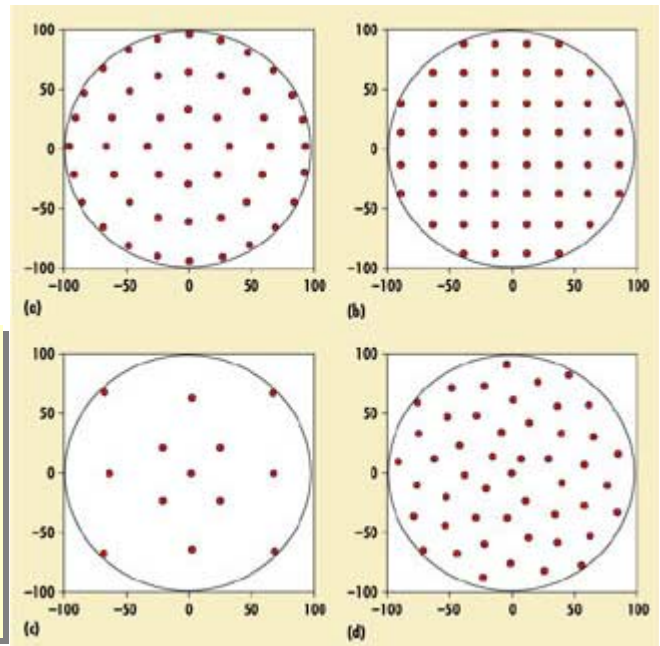
. 4 map  
polar(a) / area(b) / radial(d) map

2a polar map  
area map(2b)

가 polar map (discrete)  
가 polar pattern  
가 standard polar map (azimuthal) 가

가  
7  
2c radial 가

2.  
CMP (site selection)  
200mm ;  
(a) polar map, (b) area map, (c)  
49-point polar map  
13 site , (d) radial  
(x, y : mm)



site selection radial (2d)  
CMP  
가 site selection radial

## Radial

radial map . 1  
radial  
radial map

가

# Post-CMP Defect

radial

site selection

map 1

$$A_n = \frac{\pi(R_w - EE)^2}{n-1}$$

\* Edge Exclusion :

$R = 95 \text{ mm}$       edge exclusion       $200 \text{ mm}$   
 $5 \text{ mm}$

$R_w$

$EE$  edge exclusion

가

$$R_i = \sqrt{\frac{i A_n}{\pi}} \quad (i = 1, n-1)$$

$$x_i = R_i \cos(i\theta), \quad y_i = R_i \sin(i\theta) \quad (\theta = \quad )$$

3 13

map

x

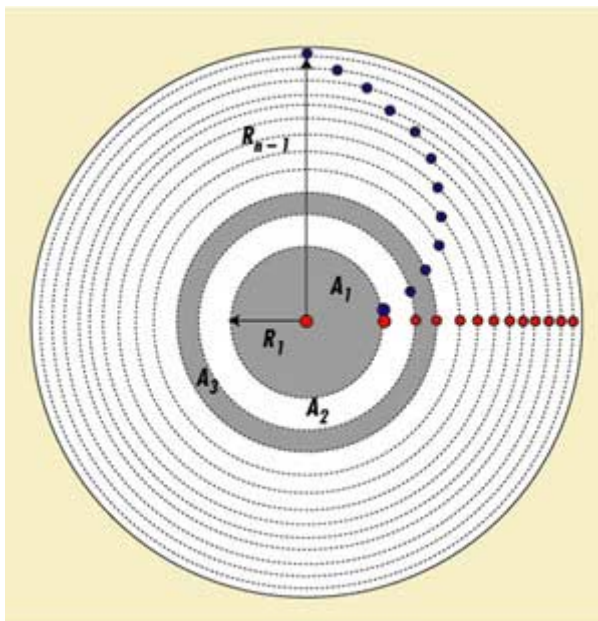
radial

2d

49

$82^\circ$

edge exclusion 3mm



3.  
 radial (n=13)  
 x  
 7.5°

# Post-CMP Defect



1      8    13                      Cartesian x, y                      .

radial/                      (azimuthal)                      .

2                      site map                      .

                    line                      가                      line scan

Measurement Pattern					
Profile Type	Area 6-mm EE	Radial 6-mm EE	Area 4-mm EE	Radial 4-mm EE	Radial 3-mm EE
Center fast	4.86	2.64	12.55	6.01	8.03
Center slow	6.48	6.73	10.29	7.75	8.00

I : n=13      radial map      site

Rodel                      Materials Integration Center                      blanket film

                    Peter Wolters                      PM200 Gemini CMP                      Speedfam-IPEC

IPEC472                      .                      가

site selection                      .

                    Rodel      colloidal silica slurry(Klebosol 1501/50)      IC1000

perforated / K-groove                      ,                      Rodel

slurry(MSW2000)      IC1000 K-groove                      .

abrasiveless                      IC1000 K-x,y groove                      .

                    Therna-Wave                      OptiProbe 2600                      ,                      /                      Creative Design

Engineering                      CDE ResMap                      .

                    CMP                      .

                    가                      가                      2500Å/min                      ,                      가 250 Å/min

                    (uniformity performance)

uniformity      10%                      .

## (Oxide Polishing)

200mm polish profile      hard carrier      passive carrier ring      CMP

3~4mm

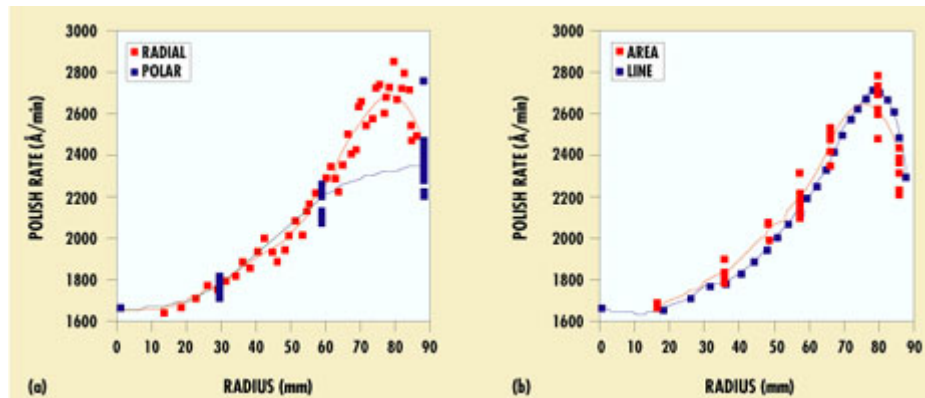
90mm

60 ~ 80mm

site selection pattern

EE가

4



4.4  
(a): radial & polar  
(b): area & line scan

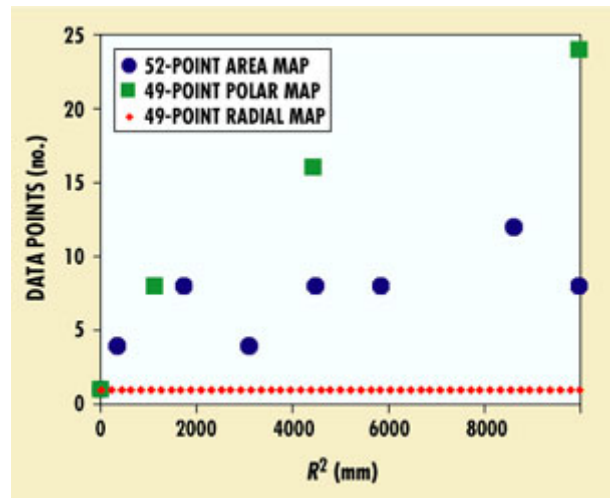
4      4      site selection  
 . 3      49      area scan      52  
 carrier      3mm EE      가      wafer  
 2      line      slow  
    (radial map, polar map, area map)  
                  λ =1000, line scan      λ =1).  
 3      radial point      7      radial point      polar & area  
          line scan      radial map  
 radial coverage      gap      polar / area  
 가

# Post-CMP Defect

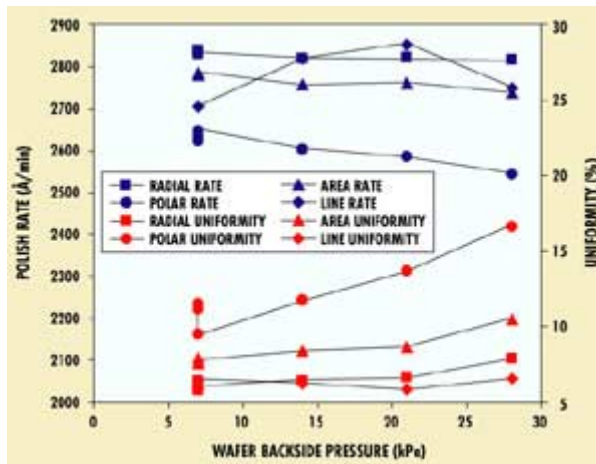


4 site selection pattern  
 . polar map  
 . line scan  
 ( radial 가 가 가 ). line scan  
 5 site selection 3  
 . 3가 가  
 radial map 가 radial  
 polar map 가  
 CMP

5. radial pattern (R<sup>2</sup>) area, polar )



6 backside  
 backside CMP uniformity 가  
 wafer carrier (外座層) polar 4 site selection 4  
 wafer notch 가



6. CMP backside uniformity

radial & polar maps map      polar map      radial map  
 가 7.3–9.9%, uniformity가 49–112%

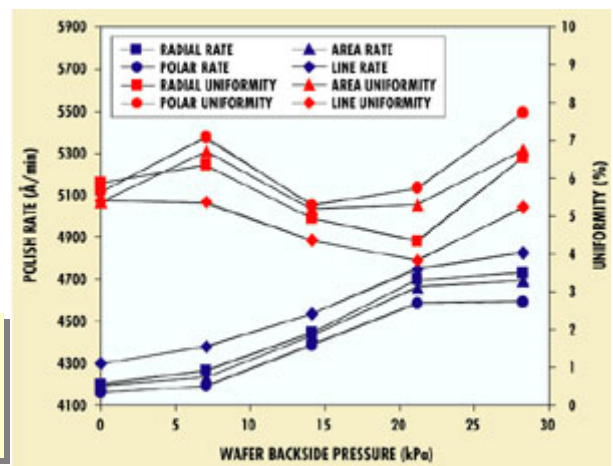
## Copper / Tungsten Polishing

EE

EE

CMP

7. Cu CMP backside uniformity data.

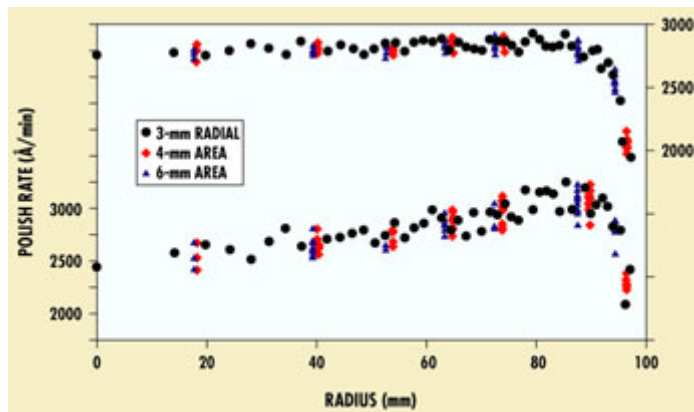


7 Cu CMP backside uniformity  
 polar map 가 3%, uniformity 32%

# Post-CMP Defect



10mm polar map 1 2가 CMP EE  
 가 4 가  
 CMP edge effects CMP 가  
 CMP EE=6mm(가 4mm) uniformity  
 down force backside pressure radial map(EE=3, 4, 6mm) area map(EE=4, 6mm)  
 7 4mm, 6mm area mapping 가  
 profile 가  
 96mm ring 96mm 8  
 leading-edge effects가 가 radial 96  
 mm 97 mm



8.

CMP

# Post-CMP Defect



2 8 2  
4mm, 6mm EE

uniformity

radial

n	3-mm EE		5-mm EE		10-mm EE	
	X 축	Y 축	x 축	Y 축	x 축	Y 축
1	0.00	0.00	0.00	0.00	0.00	0.00
2	0.00	-28.00	0.00	-27.42	0.00	-25.98
3	0.00	39.60	0.00	38.78	0.00	36.74
4	-48.50	0.00	-47.50	0.00	-45.00	0.00
5	56.00	0.00	54.85	0.00	51.96	0.00
6	44.27	-44.27	43.36	-43.36	41.08	-41.08
7	-48.50	48.50	-47.50	47.50	-45.00	45.00
8	52.39	52.39	51.31	51.31	48.61	48.61
9	-56.00	-56.00	-54.85	-54.85	-51.96	-51.96
10	0.00	-84.00	0.00	-82.27	0.00	-77.94
11	88.55	0.00	86.72	0.00	82.16	0.00
12	0.00	92.87	0.00	90.96	0.00	86.17
13	-97.00	0.00	-95.00	0.00	-90.00	0.00

2. 8

Center fast/Center slow

uniformity

EE edge effects  
robust site selection pattern

area map

uniformity  
force / low backside pressure  
4mm radial / area response  
4mm area  
uniformity가  
down force backside pressure가  
uniformity

uniformity가  
4mm / 6mm response  
low down force

9

가 high down

가  
backside pressure

3

effect  
2712 Å/min

가  
2612 Å/min

4mm area  
가 4% 가

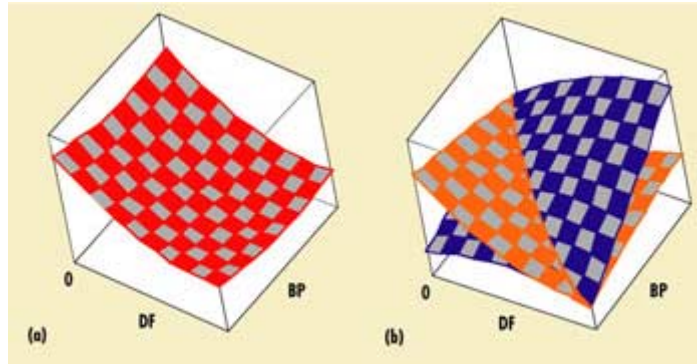
site placement  
4mm radial

4mm area  
uniformity가 108%  
2730/ 2692 Å/min

9.32%  
uniformity

4mm radial  
6mm radial / area  
2.71 / 3.45%

4.93%



9. 3가

(a) area map EE=6mm, (b) area & radial map EE=4mm.  
 backside pressure (BP) down force (DF)

radial site selection CMP  
 가 site selection radial  
 CMP /

: ([www.semipark.co.kr](http://www.semipark.co.kr)), 2002 2 21  
 : A. Scott Lawing, Process Development Engineer, Rodel